MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PIFD

MLMV324IPT

Product specification





GENERAL DESCRIPTION

The MLMV324IPT (quad)are general purpose,low offset,high frequency response andlow power op erational amplifiers. With an excellent bandwidth of 1MHz,a slew rate of1V/µs,and a quiescent cur rent of 28µA peramplifier at 5V,the MLMV324IPT family can be essigned into a wide range of app lications.

The MLMV324IPT op-amps are designed to provi deoptimal performance in low voltage and lowpo wer systems. The input common-modevoltage ran ge includes ground, and themaximum input offset voltage are 3mV. These parts provide rail-to-rail out put swing into heavyloads.

The MLMV324IPT families of operational amplifier sare specified at the full temperature range of -5 $^{\circ}$ C to +125 $^{\circ}$ C under single or dual powersuppli es of 1.5V to 5.5V.

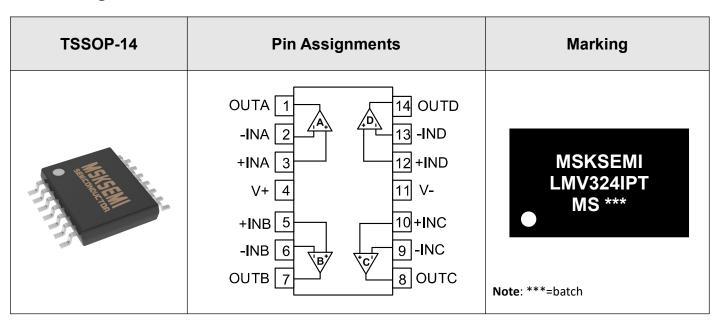
FEATURES

- Input Offset Voltage:1mV (Typical)
- Low Supply Current:28µA(Vs=5V)
- Supply Range:1.8V to 5.5V
- Gain Bandwidth:1MHz(Vs=5V)
- Slew rate:1V/us (Vs=5V)
- Rail-to-Rail Input and Output
- Low Cost
- Micro size Packages:TSSOP-14

APPLICATIONS

- Battery and Power Supply Control
- Audio Outputs
- Smoke/Gas/Environment Sensors
- Portable Equipment and Mobile Devices
- Sensor Interfaces
- Active Filters
- Medical Equipment

Pin Configuration and Functions

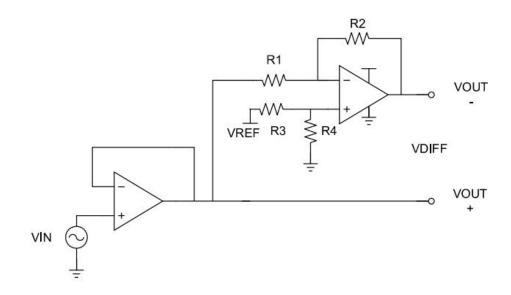




Pin Description

| PIN | | I/O | DESCRIPTION | |
|------|--------|-----|--------------------------------|--|
| NAME | Number | | DESCRIPTION | |
| +INA | 3 | | Noninverting input,channel A | |
| +INB | 5 | | Noninverting input,channel B | |
| +INC | 10 | | Noninverting input,channel C | |
| +IND | 12 | | Noninverting input,channel D | |
| -INA | 2 | | Inverting input,channel A | |
| -INB | 6 | | Inverting input,channel B | |
| -INC | 9 | | Inverting input,channel C | |
| -IND | 13 | | Inverting input,channel D | |
| OUTA | 1 | 0 | Output,channel A | |
| OUTB | 7 | 0 | Output,channel B | |
| OUTC | 8 | | Output,channel C | |
| OUTD | 14 | 0 | Output,channel D | |
| V- | 4 | | Negative (lowest)power supply | |
| V+ | 11 | _ | Positive (highest)power supply | |

TYPICAL APPLICATION





SPECIFICATIONS

Absolute Maximum Ratings(1)

| | | MIN | MAX | UNIT |
|---------------|--|--------------|------------|------|
| | Supply Voltage | | 6 | V |
| Voltage | Signal Input Terminals Voltage ⁽²⁾ | (V-) - 0.5 | (V+) + 0.5 | V |
| | Signal Input Terminals Voltage ⁽³⁾ | (V-) - 0.5 | (V+) + 0.5 | V |
| | Signal Input Terminals Current ⁽²⁾ | -10 | 10 | mA |
| Current | Signal output Terminals Current ⁽³⁾ | - 200 | 200 | mA |
| | Output Short-Circuit ⁽⁴⁾ | Continuous | | |
| | Operating Temperature Range | - 55 | 125 | °C |
| θ_{JA} | Storage Temperature Range | - 65 | 150 | °C |
| | Junction Temperature | - 40 | 150 | °C |

- (1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.
- (2) Input terminals are diode clamped to the power-supply rails. Input signals that can swing more than 0.5V beyond the supply rails should be current limited to 10mA or less.
- (3) Output terminals are diode-clamped to the power-supply rails. Output signals that can swing more than 0.5V beyond the supply rails should be current-limited to ±200mA or less.
- (4) Short-circuit to ground, one amplifier per package.

ESD Ratings

| | | | VALUE | UNIT |
|-------------|-------------------------|----------------------------|-------|----------|
| | | Human-Body Model (HBM) | ±2000 | V |
| $V_{(ESD)}$ | Electrostatic discharge | Charged-Device Model (CDM) | ±500 | V |
| | | Machine Model | 100 | ٧ |

Recommended Operating Conditions

| | | MIN | MAX | UNIT |
|-----------------|---------------|-------|-------|------|
| Supply voltage, | Single-supply | 1.5 | 5.5 | V |
| Vs= (V+) - (V-) | Dual-supply | ±0.75 | ±2.75 | V |



ELECTRICAL CHARACTERISTICS ($V_s = +5V$)

At $T_A = 25$ °C, $V_{CM}=V_{OUT}=V_S/2$, unless otherwise noted.

| | PARAMETER | CONDITIONS | MIN | TYP | MAX | UNIT |
|-------------------------------|------------------------------------|--|--------------------|-----|----------------------|------------------|
| OFFSET | VOLTAGE | | | | | |
| Vos | Input Offset Voltage | | -3 | ±1 | 3 | mV |
| dV _{OS} /dT | Input Offset Voltage Average Drift | T _A = -55°C to 125°C | | 1.8 | | μV/°C |
| INPUT C | URRENT | | | | | |
| I B | Input Bias Current | | | 5 | | pА |
| los | Input Offset Current | | | 1 | | pА |
| NOISE | , | | 1 | | | |
| V_N | Input Voltage Noise | f=0.1Hz to 10Hz | | 20 | | μV _{PP} |
| e _n | Input Voltage Noise Density | f=1kHz | | 65 | | nV/√Hz |
| INPUT V | OLTAGE | | | | | |
| V_{CM} | Common-Mode Voltage Range | | V _S 0.1 | | V _{S+} +0.1 | V |
| CMRR | Common-Mode Rejection Ratio | V _{CM} =0.1V to 4V | 70 | 80 | | dB |
| FREQUE | NCY RESPONSE | | | | | |
| GBW | Gain-Bandwidth Product | | | 1 | | MHz |
| SR | Slew Rate | G = +1, V _{IN} =2V Step | | 1 | | V/us |
| ts | Settling Time to 0.1% | G = +1, V _{IN} =2V Step | | 2.5 | | us |
| OUTPUT | | | | | | |
| A _V | Open-Loop Voltage Gain | V_{OUT} =0.1V to 4.9V R_L =100k Ω | 80 | 100 | | dB |
| V _{OUT} | Output Swing from Rail | R _L =100kΩ | | | 5 | mV |
| I _{sc} | Output Short-Circuit Current | Source current | | 45 | | mA |
| ■ 5C | Carpar Onort Onoun Ounem | Sink current | | 70 | | mA |
| C _L ⁽¹⁾ | Capacitive Load Drive | G = +1, V _{IN} =0.2V Step | | | 1000 | pF |



| POWER SUPPLY | | | | | | |
|--------------|---------------------------------|------------------------------|-----|----|-----|----|
| PSRR | Power-Supply Rejection Ratio | V _S =1.5V to 5.5V | 80 | 90 | | dB |
| Vs | Operating Voltage Range | | 1.5 | | 5.5 | V |
| IQ | Quiescent Current/Amplifier | I _O =0A | | 28 | 40 | uA |

⁽¹⁾ Capacitive load drive means that above a given maximum value, the output waveform will oscillate under the step response.



TYPICAL CHARACTERISTICS

At $T_A = 25$ °C, $V_S = +5V$, G=+1, $V_{IN}=V_{OUT}=V_S/2$, unless otherwise noted.

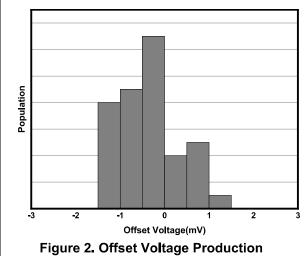


Figure 2. Offset Voltage Production
Distribution

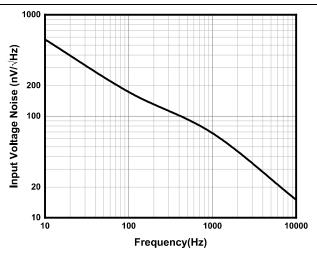


Figure 3. Input Voltage Noise Spectral Density

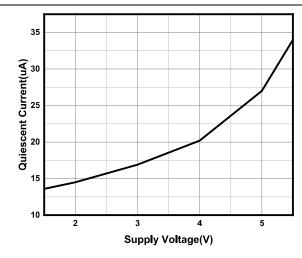


Figure 4. Quiescent Current vs Supply Voltage

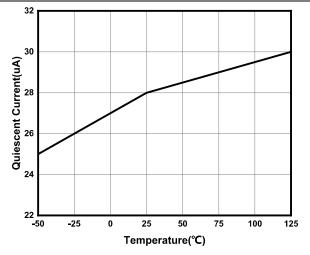


Figure 5. Quiescent Current vs Temperature

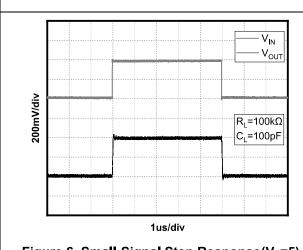


Figure 6. Small-Signal Step Response($V_S=5$)

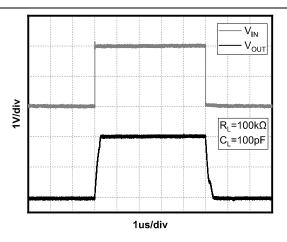
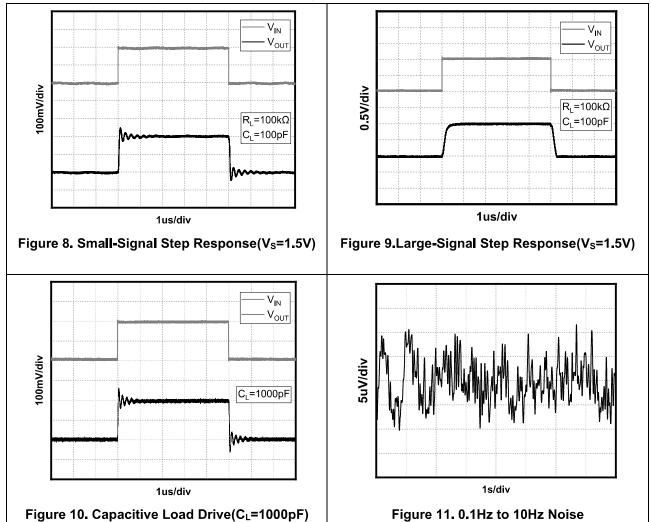


Figure 7. Large-Signal Step Response(V_S=5V)



TYPICAL CHARACTERISTICS

At $T_A = 25$ °C, $V_S = +5V$, G=+1, $V_{IN}=V_{OUT}=V_S/2$, unless otherwise noted.





Detailed Description

Oyerview

The MLMV324IPT devices are a low power,unity-gain stable,rail-to-rail operational amplifier that operate in a single-supply voltage range of 1.8V to 5.5V (±0.9V to ±2.75V). A high supply voltage of 6V(absolute maximum)can permanently damage the amplfier. Rail-to-rail input and output wobbles significantly increase the dynamic range, especially in low-supply applications. Good layout practices require that a 0.1uF capacitor be used where it is tightly threaded through the power supply pin.

Phase Reversal Protection

The MLMV324IPT devices have internal phase-reversal protection. Many op amps exhibit phase reversal when the input is driven beyond the linear common-mode range. This condition is most often encountered in noninverting circuits when the input is driven beyond the specified common-mode voltage range, causing the output to reverse into the opposite rail. The input of the MLMV324IPT prevents phase reversal with excessive commonmode voltage. Instead, the appropriate rail limits the output voltage

Typical Applications

1 Voltage Follower

As shown in Figure 12,the voltage gain is 1. With this circuit, the output voltage Vour is configured to be equal to the input voltage Vin. Due to the high input impedance and low output impedance, the circuit can also stabilize the output voltage, the output voltage expression is Detailed Descriptio

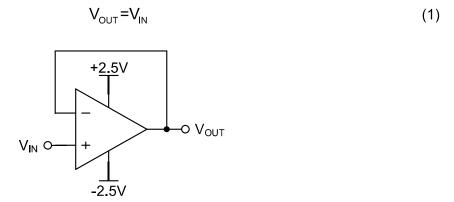


Figure 12. Voltage Follower

2 Inverting Proportional Amplifier

As shown in Figure 13, for a reverse-phase proportional amplifier, the input voltage V_{IN} is amplified by a voltage gain that depends on the ratio of R1 to R2. The output voltage V_{OUT} is inversely with the input voltage V_{IN} . The input impedance of the circuit is equal to R1, and the output voltage expression is

$$V_{OUT} = -\frac{R2}{R1} V_{IN}$$
 (2)



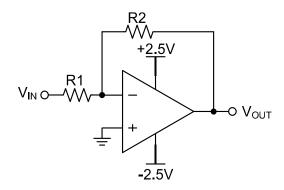


Figure 13. Inverting Proportional Amplifier

3 Noninverting Proportional Amplifier

As shown in Figure 14, for a noninverting amplifier, the input voltage V_{IN} is amplified by a voltage gain that depends on the ratio of R1 to R2. The output voltage V_{OUT} is in phase with the input voltage V_{IN} . In fact, this circuit has a high input impedance because its input side is the same as the input side of the operational amplifier. The output voltage expression is

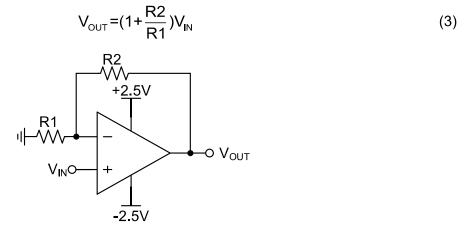


Figure 14. Noninverting Proportional Amplifier

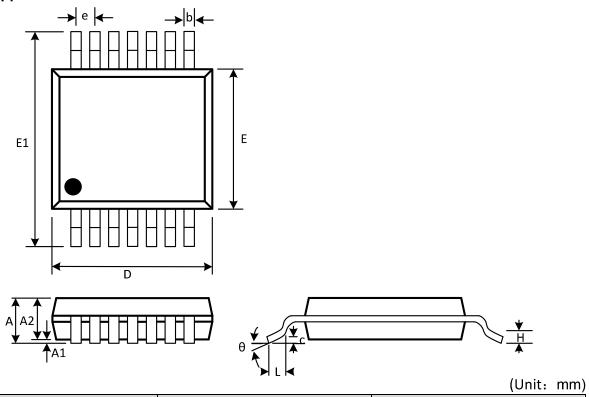
Layout Guidelines

Attention to good layout practices is always recommended. Keep traces short. When possible, use a PCB ground plane with surface-mount components placed as close to the device pins as possible. Place a 0.1uF capacitor closely across the supply pins.

These guidelines should be applied throughout the analog circuit to improve performance and provide benefits such as reducing the EMI susceptibility.



TSSOP-14



| Symbol | Min | Max | |
|--------|------------|-------|--|
| А | | 1.200 | |
| A1 | 0.050 | 0.150 | |
| A2 | 0.800 | 1.050 | |
| b | 0.190 | 0.300 | |
| С | 0.090 | 0.200 | |
| D | 4.860 | 5.100 | |
| е | 0.650(BSC) | | |
| E | 4.300 | 4.500 | |
| E1 | 6.250 | 6.550 | |
| L | 0.500 | 0.700 | |
| | 0.250(TYP) | | |
| θ | 1° | 7° | |

REEL SPECIFICATION

| P/N | PKG | QTY |
|------------|---------|------|
| MLMV324IPT | TSSOP14 | 2500 |



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